N-Channel 100-V (D-S) 200°C MOSFET

PRODUCT SUMMARY		
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
100	0.0095 @ V_{GS} = 10 V	110 [a]

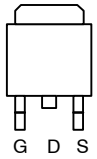
FEATURES

- TrenchFET® Power MOSFET
- 200°C Junction Temperature
- New Package with Low Thermal Resistance
- 100% R_g Tested

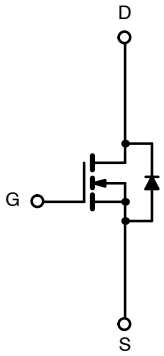
APPLICATIONS

- Automotive
  - 42-V Power Bus
  - DC/DC Conversion
  - Motor Drivers

TO-263



Top View



N-Channel MOSFET

Ordering Information: SUM110N10-09
SUM110N10-09-E3 (Lead Free)

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current (T_J = 175°C)	T_C = 25°C	I_D	110[a]	A
	T_C = 125°C		87[a]	
Pulsed Drain Current		I_{DM}	440	
Avalanche Current		I_{AR}	75	
Repetitive Avalanche Energy[b]	L = 0.1 mH	E_{AR}	280	mJ
Maximum Power Dissipation[b]	T_C = 25°C	P_D	437.5[c]	W
	T_A = 25°C[d]		3.75	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	−55 to 200	°C

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Limit	Unit
Junction-to-Ambient	PCB Mount (TO-263)[d]	R_{thJA}	40	°C/W
Junction-to-Case (Drain)		R_{thJC}	0.4	

Notes
a. Package limited.
b. Duty cycle ≤ 1%.
c. See SOA curve for voltage derating.
d. When mounted on 1" square PCB (FR-4 material).

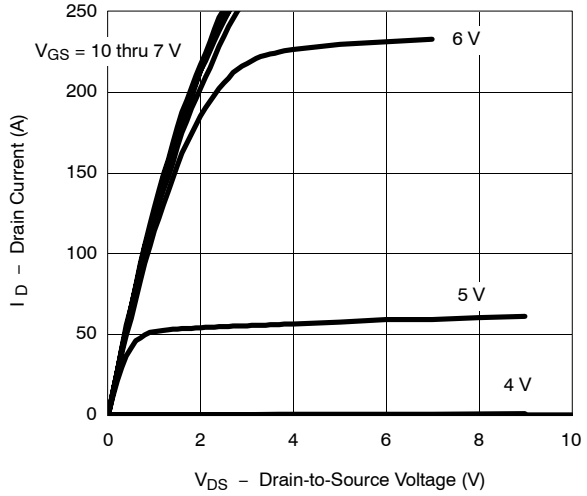
SPECIFICATIONS (T_J =25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{DS} = 0 V, I_D = 250 μA	100			V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	2		4	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 100 V, V_{GS} = 0 V			1	μA
		V_{DS} = 100 V, V_{GS} = 0 V, T_J = 125°C			50	
		V_{DS} = 100 V, V_{GS} = 0 V, T_J = 200°C			10	mA
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 10 V	120			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 30 A		0.0078	0.0095	Ω
		V_{GS} = 10 V, I_D = 30 A, T_J = 125°C			0.017	
		V_{GS} = 10 V, I_D = 30 A, T_J = 200°C			0.025	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 30 A	25			S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		6700		pF
Output Capacitance	C_{oss}			750		
Reverse Transfer Capacitance	C_{rss}			280		
Total Gate Charge[c]	Q_g	V_{DS} = 50 V, V_{GS} = 10 V, I_D = 85 A		110	160	nC
Gate-Source Charge[c]	Q_{gs}			24		
Gate-Drain Charge[c]	Q_{gd}			24		
Gate Resistance	R_g		1.5		6.2	Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 50 V, R_L = 0.6 Ω I_D ≅ 85 A, V_{GEN} = 10 V, R_g = 2.5 Ω		20	30	ns
Rise Time[c]	t_r			125	200	
Turn-Off Delay Time[c]	$t_{d(off)}$			55	85	
Fall Time[c]	t_f			130	195	
Source-Drain Diode Ratings and Characteristics (T_C = 25°C)[b]						
Continuous Current	I_S				110	A
Pulsed Current	I_{SM}				240	
Forward Voltage[a]	V_{SD}	I_F = 85 A, V_{GS} = 0 V		1.0	1.5	V
Reverse Recovery Time	t_{rr}	I_F = 50 A, di/dt = 100 A/μs		70	140	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			5.5	10	A
Reverse Recovery Charge	Q_{rr}			0.19	0.35	μC

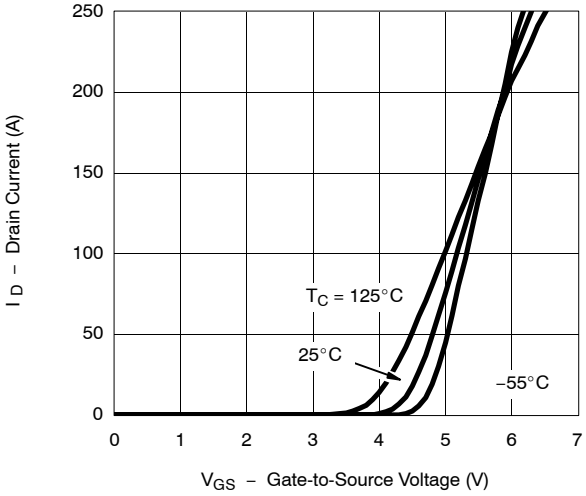
Notes
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

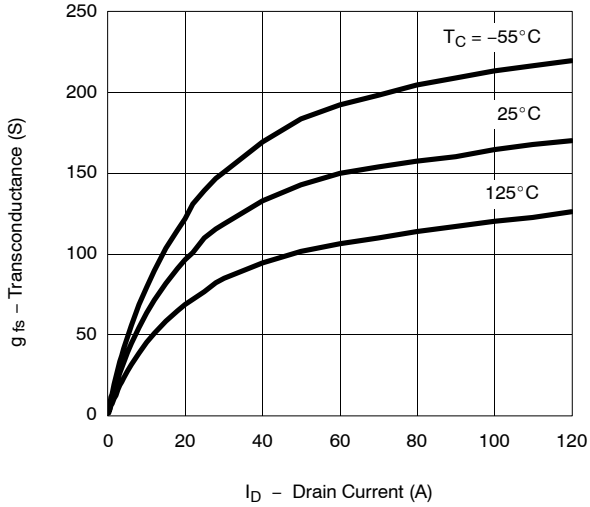
Output Characteristics



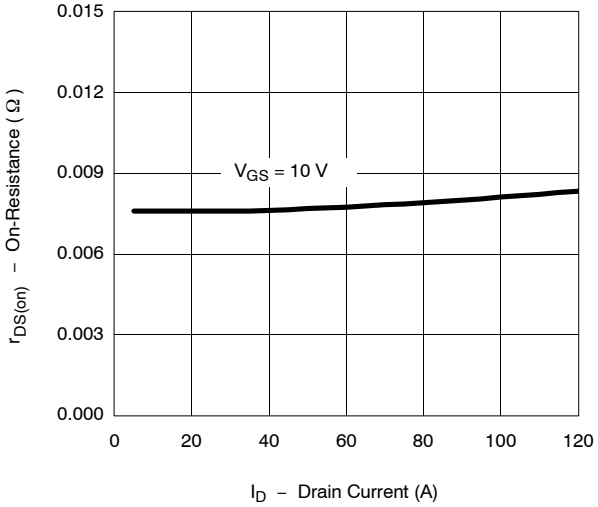
Transfer Characteristics



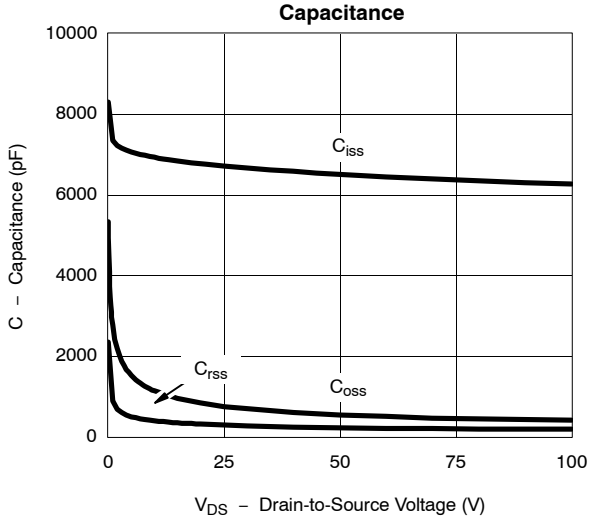
Transconductance



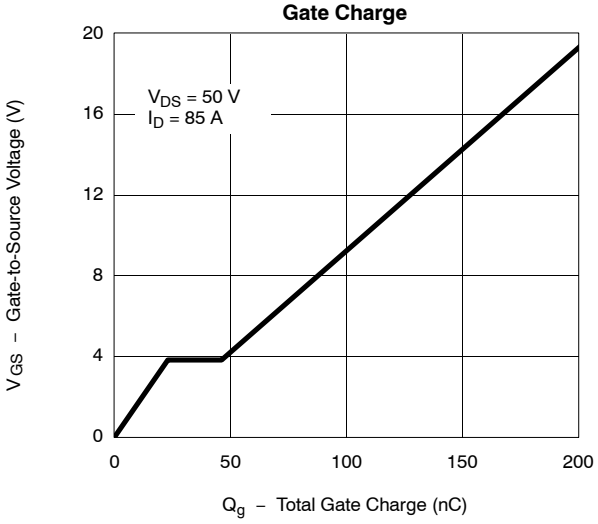
On-Resistance vs. Drain Current



Capacitance

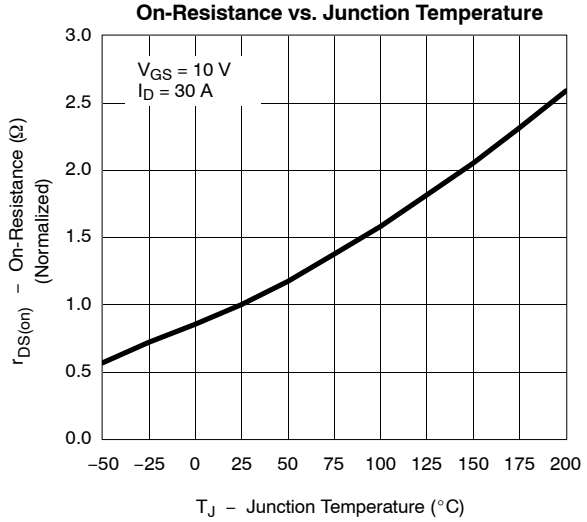


Gate Charge

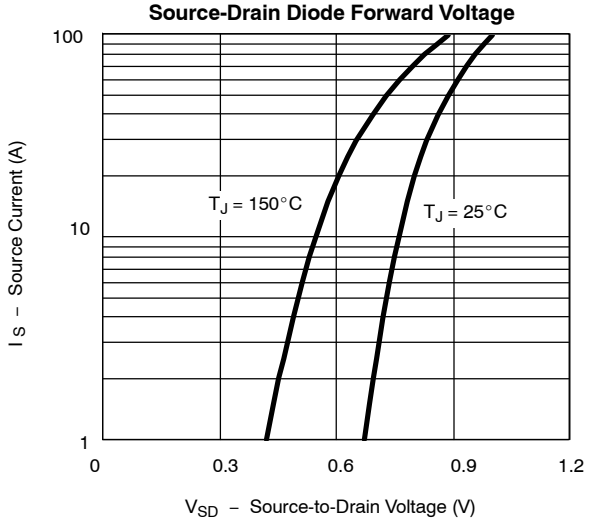


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

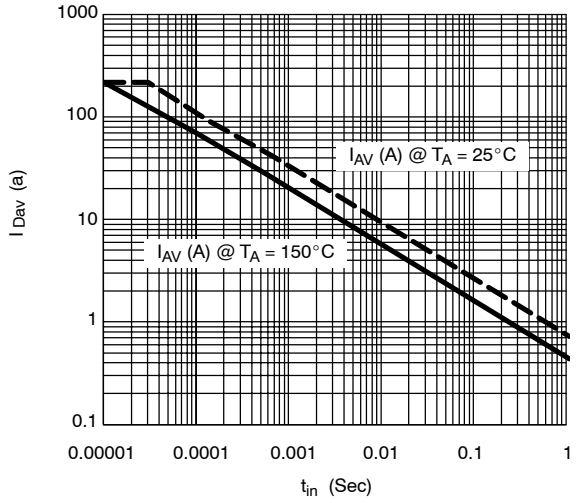
On-Resistance vs. Junction Temperature



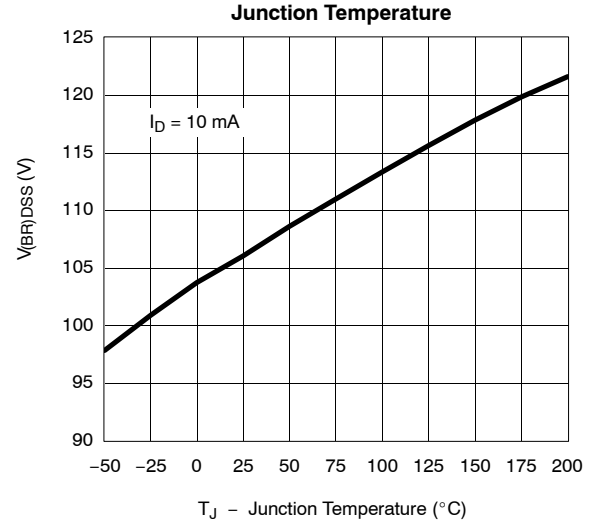
Source-Drain Diode Forward Voltage



Avalanche Current vs. Time

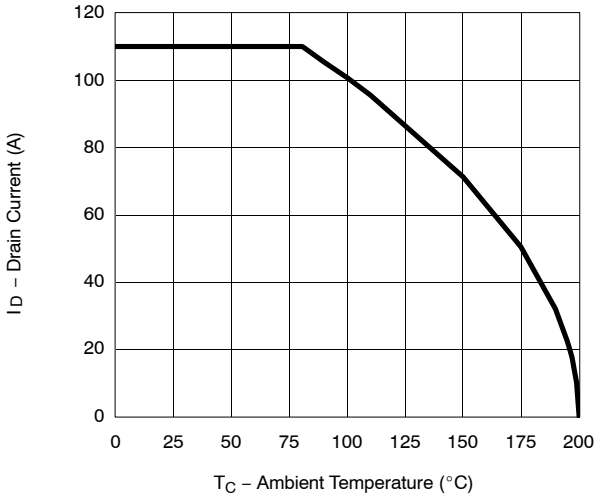


Drain Source Breakdown vs. Junction Temperature

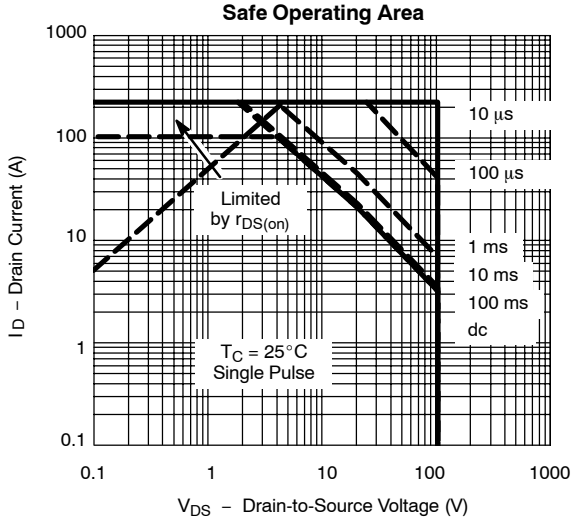


THERMAL RATINGS

Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case